

PJE138L

60V N-Channel Enhancement Mode MOSFET

Voltage

60 V

Current

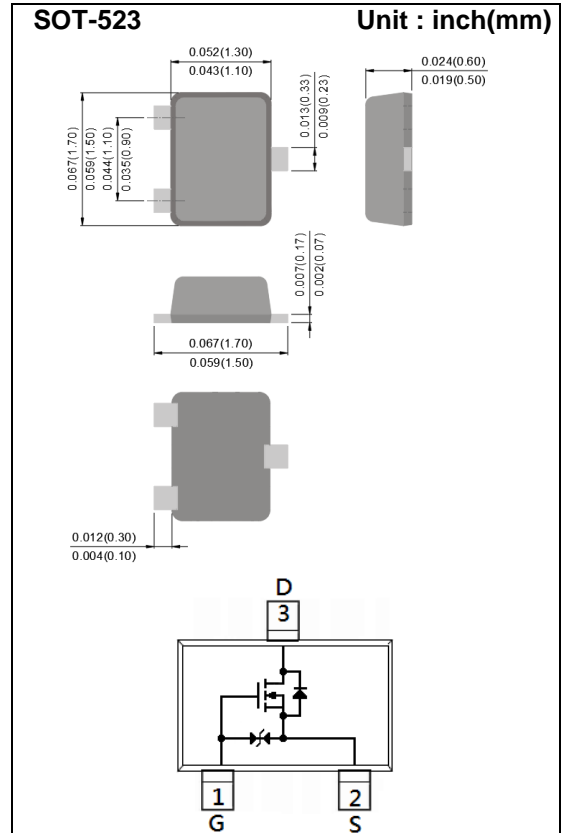
160mA

Features

- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@160mA < 4.2\Omega$
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_D@100mA < 5\Omega$
- $R_{DS(ON)}$, $V_{GS}@2.5V$, $I_D@50mA < 7\Omega$
- Advanced Trench Process Technology
- ESD Protected
- Specially Designed for Relay driver, Speed line drive, etc.
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : SOT-523 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.002 grams
- Marking : E8L



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

| PARAMETER | | SYMBOL | LIMIT | UNITS |
|--|---------------------------------|-----------------|---------|---------------------------|
| Drain-Source Voltage | | V_{DS} | 60 | V |
| Gate-Source Voltage | | V_{GS} | +20 | V |
| Continuous Drain Current | | I_D | 160 | mA |
| Pulsed Drain Current | | I_{DM} | 800 | mA |
| Power Dissipation | $T_A=25^\circ\text{C}$ | P_D | 223 | mW |
| | Derate above 25°C | | 1.8 | mW/ $^\circ\text{C}$ |
| Operating Junction and Storage Temperature Range | | T_J, T_{STG} | -55~150 | $^\circ\text{C}$ |
| Typical Thermal Resistance | | $R_{\theta JA}$ | 560 | $^\circ\text{C}/\text{W}$ |
| - Junction to Ambient ^(Note 3) | | | | |

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Electrical Characteristics (T_A=25°C unless otherwise noted)

| PARAMETER | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNITS |
|---|---------------------|--|------|------|------|-------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V, I _D =250uA | 60 | - | - | V |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D =250uA | 0.8 | 1.2 | 1.5 | V |
| Drain-Source On-State Resistance | R _{DS(on)} | V _{GS} =10V, I _D =160mA | - | 2.5 | 4.2 | Ω |
| | | V _{GS} =4.5V, I _D =100mA | - | 2.8 | 5 | |
| | | V _{GS} =2.5V, I _D =50mA | - | 3.7 | 7 | |
| | | V _{GS} =1.8V, I _D =10mA | - | 12 | - | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =60V, V _{GS} =0V | - | 0.01 | 1 | uA |
| Gate-Source Leakage Current | I _{GSS} | V _{GS} =±20V, V _{DS} =0V | - | ±1.0 | ±10 | uA |
| Dynamic (Note 4) | | | | | | |
| Total Gate Charge | Q _g | V _{DS} =15V, I _D =160mA, V _{GS} =4.5V (Note 1,2) | - | 0.7 | - | nC |
| Gate-Source Charge | Q _{gs} | | - | 0.33 | - | |
| Gate-Drain Charge | Q _{gd} | | - | 0.2 | - | |
| Input Capacitance | C _{iss} | V _{DS} =15V, V _{GS} =0V, f=1.0MHZ | - | 15 | - | pF |
| Output Capacitance | C _{oss} | | - | 8.4 | - | |
| Reverse Transfer Capacitance | C _{rss} | | - | 4.2 | - | |
| Turn-On Delay Time | t _{d(on)} | V _{DD} =10V, I _D =160mA, V _{GS} =10V, R _G =6Ω (Note 1,2) | - | 7 | - | ns |
| Turn-On Rise Time | t _r | | - | 22 | - | |
| Turn-Off Delay Time | t _{d(off)} | | - | 21 | - | |
| Turn-Off Fall Time | t _f | | - | 25 | - | |
| Drain-Source Diode | | | | | | |
| Maximum Continuous Drain-Source Diode Forward Current | I _S | --- | - | - | 160 | mA |
| Diode Forward Voltage | V _{SD} | I _S =160mA, V _{GS} =0V | - | 0.8 | 1.1 | V |

NOTES :

1. Pulse width ≤ 300us, Duty cycle ≤ 2%
2. Essentially independent of operating temperature typical characteristics.
3. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. mounted on a 1 inch square pad of copper
4. Guaranteed by design, not subject to production testing.

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TYPICAL CHARACTERISTIC CURVES

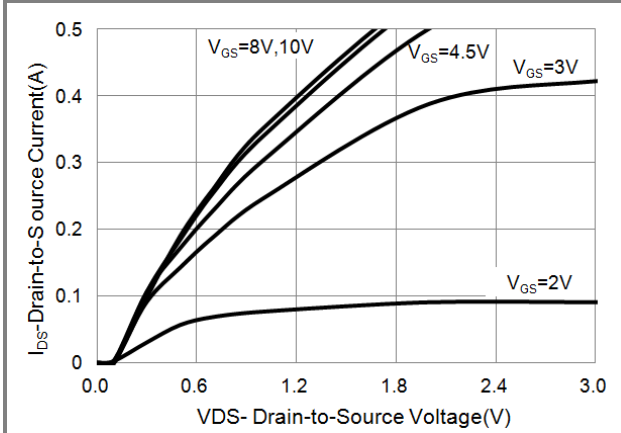


Fig.1 On-Region Characteristics

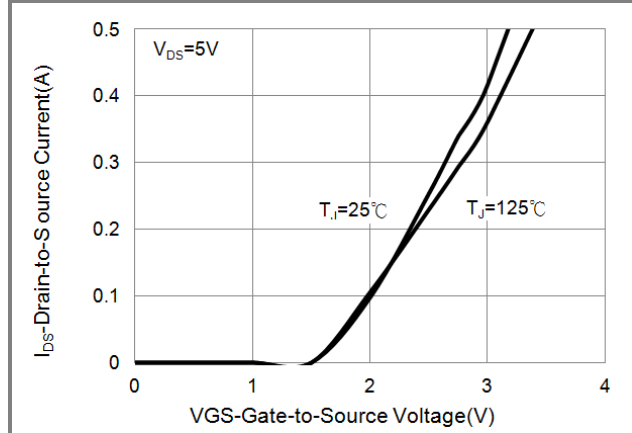


Fig.2 Transfer Characteristics

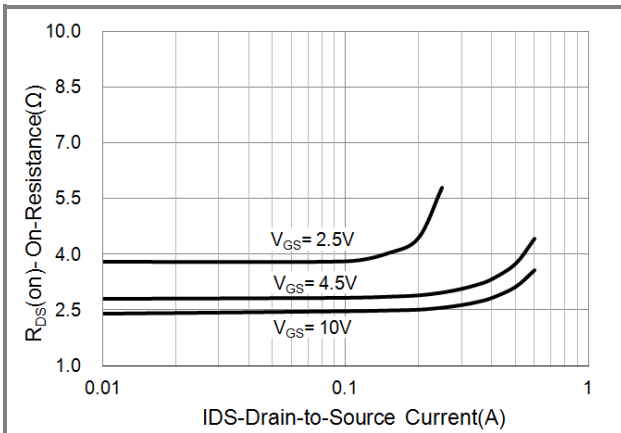


Fig.3 On-Resistance vs. Drain Current

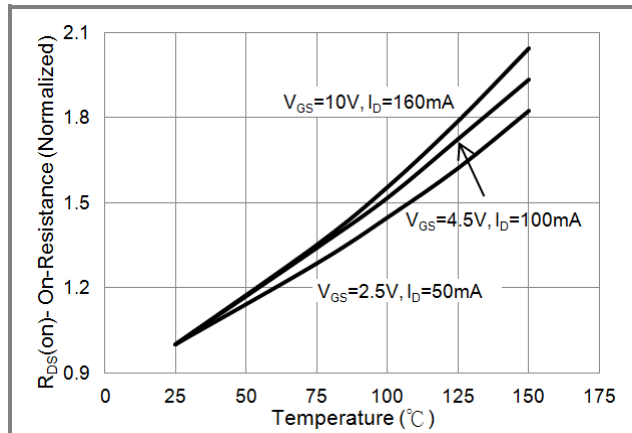


Fig.4 On-Resistance vs. Junction temperature

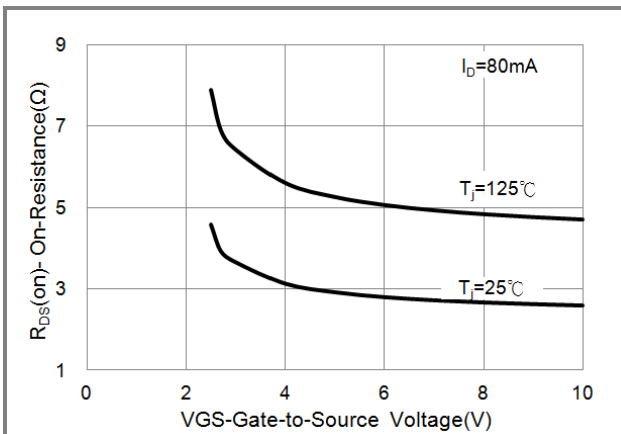


Fig.5 On-Resistance Variation with VGS.

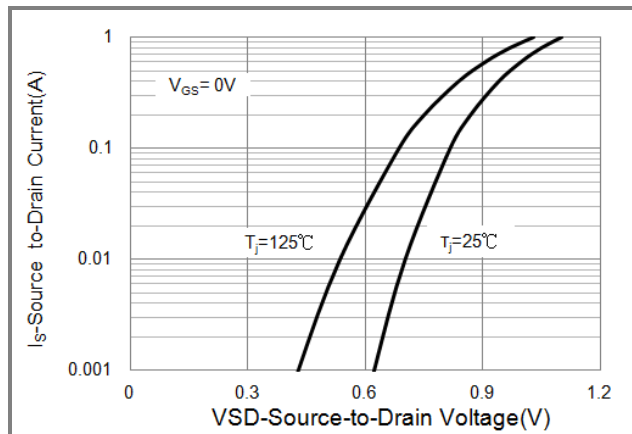


Fig.6 Body Diode Characteristics

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TYPICAL CHARACTERISTIC CURVES

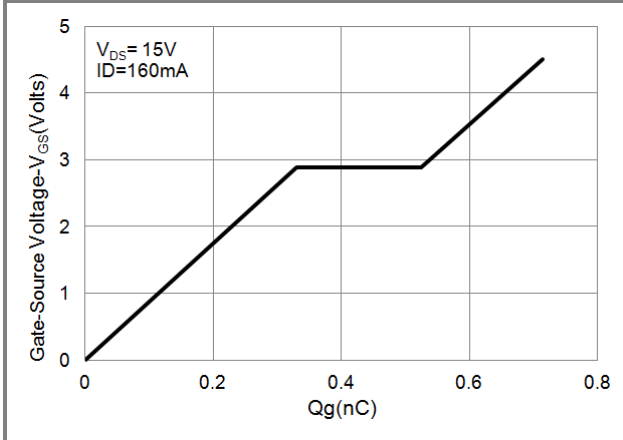


Fig.7 Gate-Charge Characteristics

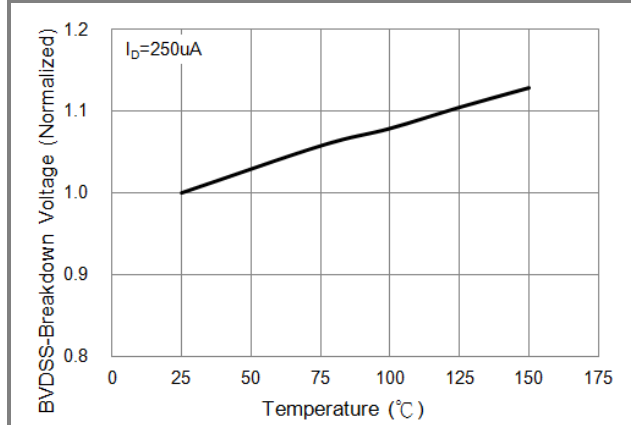


Fig.8 Breakdown Voltage Variation vs. Temperature

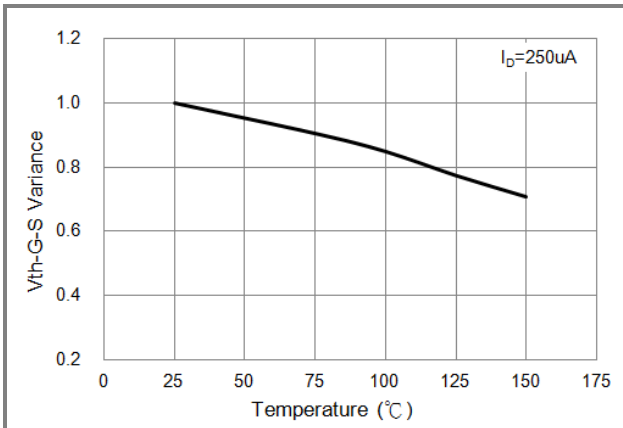


Fig.9 Threshold Voltage Variation with Temperature.

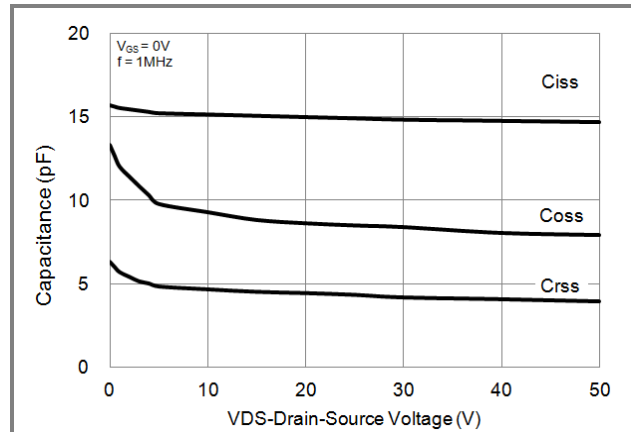


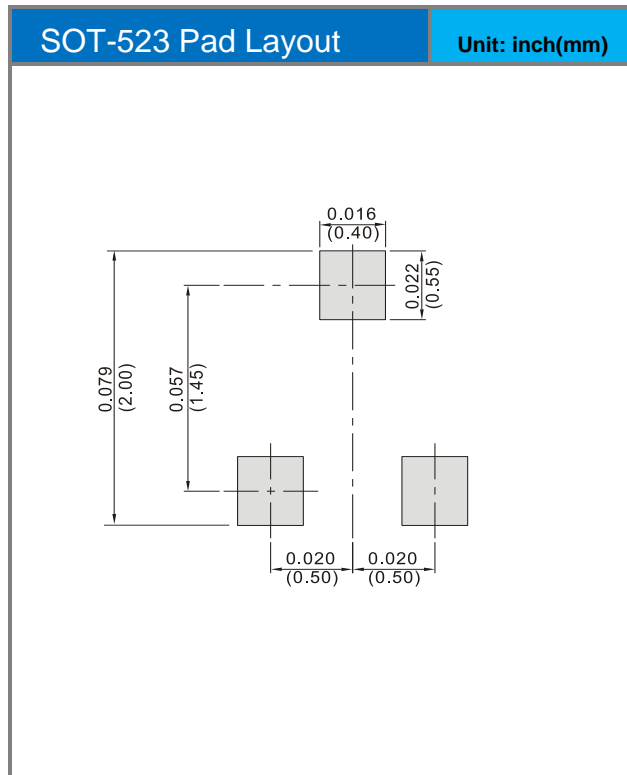
Fig.10 Capacitance vs. Drain-Source Voltage.

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Product and Packing Information

| Part No. | Package Type | Packing Type | Marking |
|----------|--------------|------------------|---------|
| PJE138L | SOT-523 | 4K pcs / 7" reel | E8L |

Mounting Pad Layout



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